Si3861BDV vs. Si3861DV

Description: Load Switch with Level-Shift
Package: TSOP-6
Pin Out: Identical

Part Number Replacements:
Si3861BDV-T1-E3 Replaces Si3861DV-T1-E3
Si3861BDV-T1-E3 Replaces Si3861DV-T1

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**Si3861BDV**	**Si3861DV**	**Unit**
Input Voltage		V_{IN}	20	20	V
ON/OFF Voltage		$V_{ON/OFF}$	8	8	
Load Current	Continuous	I_L	± 2.3	± 2.3	A
	Pulsed		± 4	± 4	
Continuous Intrinsic Diode Conduction		I_S	- 1	- 1	
Power Dissipation		P_D	0.83	0.83	W
Operating Junction and Storage Temperature Range		T_j and T_{stg}	- 55 to 150	- 55 to 150	°C
Maximum Junction-to-Ambient		R_{thJA}	150	150	°C/W

SPECIFICATIONS T_J = 25 °C, unless otherwise noted									
Parameter		**Symbol**	**Si3861BDV**			**Si3861DV**			**Unit**
			Min	**Typ**	**Max**	**Min**	**Typ**	**Max**	
OFF Characteristic									
Reverse Leakage Current		I_{FL}			1			1	µA
Diode Forward Voltage		V_{SD}		- 0.8	- 1		- 0.8	- 1	V
Dynamic									
Input Voltage Range		V_{IN}	4.5		20	4.5		20	nC
On-Resistance (P-Channel) at 1 A	V_{IN} = 10 V	$r_{DS(on)}$		0.060	0.075		0.085	0.105	Ω
	V_{IN} = 5.0 V			0.096	0.120		0.123	0.150	
	V_{IN} = 4.5 V			0.115	0.145		0.145	0.175	
On-State (P-Channel) Drain-Current	V_{IN} = 10 V	$I_{D(on)}$	1			1			A
	V_{IN} = 5 V		1			1			

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.